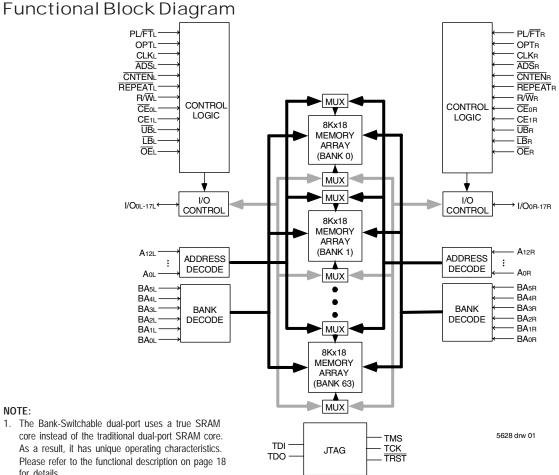
DT

HIGH-SPEED 3.3V 512K x 18 **SYNCHRONOUS BANK-SWITCHABLE DUAL-PORT STATIC RAM** WITH 3.3V OR 2.5V INTERFACE

Features:

- ٠ 512K x 18 Synchronous Bank-Switchable Dual-ported **SRAM Architecture**
 - 64 independent 8K x 18 banks
- 9 megabits of memory on chip
- Bank access controlled via bank address pins
- High-speed data access
 - Commercial: 3.4ns (200MHz)/3.6ns (166MHz)/ 4.2ns (133MHz) (max.)
 - Industrial: 3.6ns (166MHz)/4.2ns (133MHz) (max.)
- Selectable Pipelined or Flow-Through output mode
- Counter enable and repeat features
- Dual chip enables allow for depth expansion without additional logic
- Full synchronous operation on both ports ٠
 - 5ns cycle time, 200MHz operation (14Gbps bandwidth)
 - Fast 3.4ns clock to data out

- 1.5ns setup to clock and 0.5ns hold on all control, data, and address inputs @ 200MHz
- Data input, address, byte enable and control registers - Self-timed write allows fast cycle time
- Separate byte controls for multiplexed bus and bus matching compatibility
- LVTTL- compatible, 3.3V (±150mV) power supply for core
- LVTTL compatible, selectable 3.3V (±150mV) or 2.5V (±100mV) power supply for I/Os and control signals on each port
- ٠ Industrial temperature range (-40°C to +85°C) is available at 166MHz and 133MHz
- Available in 208-pin fine pitch Ball Grid Array (fpBGA) and 256-pin Ball Grid Array (BGA)
- Supports JTAG features compliant with IEEE 1149.1
- Green parts available, see ordering information



NOTE:

1. The Bank-Switchable dual-port uses a true SRAM core instead of the traditional dual-port SRAM core. As a result, it has unique operating characteristics. Please refer to the functional description on page 18 for details.

APRIL 2010

IDT70V7339S

High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Description:

The IDT70V7339 is a high-speed 512Kx18 (9Mbit) synchronous Bank-Switchable Dual-Ported SRAM organized into 64 independent 8Kx18 banks. The device has two independent ports with separate control, address, and I/O pins for each port, allowing each port to access any 8Kx18 memory block not already accessed by the other port. Accesses by the ports into specific banks are controlled via the bank address pins under the user's direct control.

Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70V7339 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by CE0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. The dual chip enables also facilitate depth expansion.

The 70V7339 can support an operating voltage of either 3.3V or 2.5V on one or both ports, controllable by the OPT pins. The power supply for the core of the device(VDD) remains at 3.3V. Please refer also to the functional description on page 18.

Pin Configuration^(1,2,3,4)

11/20/01

A1	A2	A3	A4	A5	A6	A7	A8	A9	A10	A11	A12	A13	A14	A15	A16	A17													
IO9L	NC	Vss	TDO	NC	ВАзL	A12L	A8L	NC	Vdd	CLK∟	CNTENL	A4L	Aol	OPT∟	NC	Vss													
B1 NC	B2 Vss	B3 NC	^{B4} TDI	^{B5} BA4L	B6 BA0L	B7 A9L	B8 NC	B9 CEOL	B10 Vss	^{B11} ADSL	B12 A5L	B13 A1L	B14 Vss	B15 VDDQR	B16 I/O8L	B17 NC													
C1 Vddql	C2 I/O9R	C3 Vddqr	C4 PL/FT∟	C5 BA5L	C6 BA1L	C7 A10L	C8 UBL	C9 CE1L	C10 Vss	C11 R/WL	C12 A6L	C13 A2L	C14 VDD	C15 I/O8R	C16 NC	C17 VSS													
D1 NC	D2 Vss	d3 I/O10L	D4 NC	d5 BA2L										d15 Vddql	d16 I/O7l	D17 I/O7R													
e1 I/O11L	E2 NC	e3 Vddqr	e4 I/O10R					•		•	•		E14 I/O6L	E15 NC	E16 VSS	E17 NC													
F1 Vddql	f2 I/O11R	F3 NC	F4 Vss										F14 Vss	f15 I/O6R	F16 NC	F17 Vddqr													
G1 NC	G2 VSS	g3 I/O12L	G4 NC										G14 NC	G15 VDDQL	G16 I/O5L	G17 NC													
H1 VDD	H2 NC	H3 Vddqr	H4 I/O12R		70V7339BF														70V7339BF BF-208 ⁽⁵⁾							H14 VDD	H15 NC	H16 Vss	h17 I/O5r
j1 Vddql	J2 Vdd	_{J3} Vss	J4 Vss					Pin fp					J14 Vss	J15 Vdd	J16 Vss	J17 Vddqr													
K1 I/O14R	к2 Vss	k3 I/O13r	K4 Vss					o Viev		l I			K14 I/O3R	k15 Vddql	K16 I/O4R	K17 Vss													
L1 NC	l2 I/O14L	l3 Vddqr	l4 I/O13l										L14 NC	l15 I/O3l	L16 VSS	l17 I/O4l													
M1 Vddql	M2 NC	M3 I/O15R	M4 Vss										M14 Vss	M15 NC	м16 I/O2R	M17 Vddqr													
N1 NC	N2 Vss	N3 NC	N4 I/O15L										N14 I/O1R	N15 Vddql	N16 NC	N17 I/O2L													
p1 I/O16R	p2 I/O16L	P3 Vddqr	P4 NC	^{P5} TRST	^{Р6} ВАзв	P7 A12R	P8 A8R	P9 NC	P10 VDD	P11 CLKR	P12 CNTENR	P13 A4R	P14 NC	P15 I/O1L	P16 Vss	P17 NC													
R1 VSS	R2 NC	r3 I/O17r	^{R4} TCK	^{R5} BA4R	a ha ha ha ha hua hua hua								R14 Vss	ri Vddql	r16 I/Oor	r17 Vddqr													
T1 NC	t2 I/O17L	t3 Vddql	^{T4} TMS	t5 BA 5R	T6 BA1R	T7 A10R	t8 UBr	T9 CE1R	T10 Vss	t11 R/Wr	T12 A 6R	T13 A2R	T14 Vss	T15 NC	^{T16} Vss	T17 NC													
U1 Vss	U2 NC	us PL/FTR	U4 NC	U5 BA2R	U6 A11R	U7 A7R	us LBr	U9 Vdd	U10 OER	U11 REPEATR	U12 A3R	U13 Aor	U14 Vdd	U15 OPTR	U16 NC	U17 I/Ool													

5628 drw 02c

- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 15mm x 15mm x 1.4mm with 0.8mm ball pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM

Pin Configuration^(1,2,3,4) (con't.)

70V7339BC BC-256⁽⁵⁾

256-Pin BGA Top View⁽⁶⁾

11/20/01

11/20/01															
A1	^{A2}	A3	^{A4}	^{A5}	A6	A7	A8	^{A9}	A10	A11	A12	A13	A14	A15	A16
NC	TDI	NC	BA4L	BA1∟	A11L	A 8L	NC	CE1L	OEL	CNTENL	A 5L	A 2L	A0L	NC	NC
^{B1} NC	^{B2} NC	^{B3} TDO	B4 BA5L	^{B5} BA2L	B6 A12L	B7 A9L	^{B8} ŪB∟	B9 CE0L	^{B10} R∕WL	B11 REPEATL	B12 A4L	B13 A1L	^{B14} VDD	B15 NC	^{B16} NC
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	C11	C12	C13	C14	C15	C16
NC	I/O9L	Vss	BA3L	BA0L	A10L	A7L	NC	TBL	CLKL	ADSL	A6L	A3L	OPT∟	NC	I/O8L
D1	d2	D3	d4	d5	de	d7	d8	d9	d10	d11	d12	D13	D14	D15	D16
NC	I/O9r	NC	PL/FTL	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vdd	NC	NC	I/O 8R
e1	e2	E3	e4	e5	e6	e7	E8	^{E9}	E10	E11	e12	e13	E14	e15	e16
I/O10r	I/O10L	NC	Vddql	Vdd	Vdd	Vss	Vss	Vss	Vss	VDD	Vdd	Vddqr	NC	I/O7l	I/O7r
f1	F2	F3	f4	f5	F6	F7	F8	^{F9}	F10	F11	F12	f13	F14	^{F15}	F16
I/O11L	NC	I/O1 1R	Vddql	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddqr	I/O6R	NC	I/O6L
G1	^{G2}	G3	G4	_{G5}	_{G6}	G7	G8	^{G9}	G10	G11	G12	G13	G14	G15	G16
NC	NC	I/O12L	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/ O 5L	NC	NC
H1	H2	нз	h4	H5	H6	^{H7}	на	H9	H10	H11	H12	h13	H14	H15	h16
NC	I/O12R	NC	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	NC	NC	I/O5r
J1	J2	j3	j4	_{J5}	_{J6}	J7	_{J8}	^{J9}	J10	J11	J12	j13	j14	j15	J16
I∕O13∟	I/O14R	I/O13R	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O4r	I/O3r	I/O4L
K1	K2	кз	k4	^{K5}	K6	к7	ка	^{K9}	K10	K11	K12	K13	K14	K15	к16
NC	NC	I/O14L	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	NC	NC	І/Оз∟
l1	L2	l3	l4	l5	L6	L7	L8	L9	L10	L11	l12	l13	l14	L15	l16
I/O15L	NC	I/O15R	Vddqr	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddql	I/O2l	NC	I/O2R
м1	m2	^{мз}	M4	M5	M6	M7	M8	M9	M10	M11	M12	M13	м14	м15	M16
I/O16R	I/O16L	NC	Vddqr	Vdd	Vdd	Vss	Vss	Vss	Vss	VDD	Vdd	Vddql	I/O1R	I/O1L	NC
N1	N2	N3	N4	N5	ng	N7	n8	N9	n10	N11	N12	N13	N14	n15	N16
NC	I/O17R	NC	PL/FTR	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vdd	NC	I/Oor	NC
P1	P2	P3	^р	P5	P6	P7	P8	P9	P10	P11	P12	P13	P14	P15	P16
NC	I/O17L	TMS	ВАзк	BA0R	A10R	A7R	NC	TBR	CLKR	ADSR	A 6R	A3R	NC	NC	I/Ool
^{R1}	R2	^{R3}	R4	r5	R6	R7	r8	r9	^{R10}	ri 1	R12	R13	^{R14}	^{R15}	^{R16}
NC	NC	TRST	BA5R	BA2r	A12R	A 9R	UBr	CEor	R/WR	Repeatr	A 4R	A1R	OPTr	NC	NC
T1	T2	тз	t4	t5	т6	T7	T8	^{T9}	T10	t11	T12	T13	T14	T15	^{T16}
NC	TCK	NC	B A 4r	BA 1R	А11R	A 8R	NC	CE1R	OER	CNTENR	A 5R	A 2R	A 0R	NC	NC
										•	•	•	•		

5628 drw 02d

NOTES:

1. All VDD pins must be connected to 3.3V power supply.

2. All VDDC pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).

- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

IDT70V7339S

High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Pin Names

Left Port	Right Port	Names
CEOL, CE1L	CEOR, CE1R	Chip Enables
R/WL	R/Wr	Read/Write Enable
OEL	ŌĒr	Output Enable
BAOL - BA5L	BAOR - BA5R	Bank Address ⁽⁴⁾
Aol - A12l	Aor - A12r	Address
1/Ool - 1/O17L	I/O0r - I/O17r	Data Input/Output
CLKL	CLKR	Clock
PL/FTL	PL/FTR	Pipeline/Flow-Through
ADSL	ĀDSR	Address Strobe Enable
		Counter Enable
REPEATL	REPEATR	Counter Repeat ⁽³⁾
LBL, UBL	$\overline{LB}RR, \overline{UB}RR$	Byte Enables (9-bit bytes)
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽¹⁾
OPTL	OPTR	Option for selecting VDDax ^(1,2)
V	DD	Power (3.3V) ⁽¹⁾
V	ss	Ground (0V)
T	DI	Test Data Input
Т	DO	Test Data Output
ТСК		Test Logic Clock (10MHz)
TMS		Test Mode Select
TF	RST	Reset (Initialize TAP Controller)

5628 tbl 01

- 1. VDD, OPTx, and VDDox must be set to appropriate operating levels prior to applying inputs on the I/Os and controls for that port.
- 2. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to VIH (3.3V), then that port's I/Os and controls will operate at 3.3V levels and VDD0x must be supplied at 3.3V. If OPTx is set to VIL (0V), then that port's I/Os and address controls will operate at 2.5V levels and VDD0x must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.
- 3. When REPEATx is asserted, the counter will reset to the last valid address loaded via ADSx.
- 4. Accesses by the ports into specific banks are controlled by the bank address pins under the user's direct control: each port can access any bank of memory with the shared array that is not currently being accessed by the opposite port (i.e., BA0L BA5L ≠ BA0R BA5R). In the event that both ports try to access the same bank at the same time, neither access will be valid, and data at the two specific addresses targeted by the ports within that bank may be corrupted (in the case that either or both ports are writing) or may result in invalid output (in the case that both ports are trying to read).

IDT70V7339S High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM Industr

Industrial and Commercial Temperature Ranges

Truth Table I—Read/Write and Enable Control^(1,2,3,4)

OE ³	CLK	Ē₽	CE1	ŪB	LΒ	R/W	Upper Byte I/O9-17	Lower Byte I/O0-8	MODE
Х	\uparrow	Н	Х	Х	Х	Х	High-Z	High-Z	Deselected-Power Down
Х	\uparrow	Х	L	Х	Х	Х	High-Z	High-Z	Deselected-Power Down
Х	\uparrow	L	Н	Н	Н	Х	High-Z	High-Z	All Bytes Deselected
Х	\uparrow	L	Н	Н	L	L	High-Z	Din	Write to Lower Byte Only
Х	\uparrow	L	Н	L	Н	L	Din	High-Z	Write to Upper Byte Only
Х	\uparrow	L	Н	L	L	L	Din	Din	Write to both Bytes
L	\uparrow	L	Н	Н	L	Н	High-Z	Dout	Read Lower Byte Only
L	\uparrow	L	Н	L	Н	Н	Dout	High-Z	Read Upper Byte Only
L	\uparrow	L	Н	L	L	Н	Dout	Dout	Read both Bytes
Н	Х	Х	Х	Х	Х	Х	High-Z	High-Z	Outputs Disabled

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. ADS, CNTEN, REPEAT are set as appropriate for address access. Refer to Truth Table II for details.

3. OE is an asynchronous input signal.

4. It is possible to read or write any combination of bytes during a given access. A few representative samples have been illustrated here.

Address	Previous Address	Addr Used	CLK	ADS	CNTEN	REPEAT ⁽⁶⁾	I/O ⁽³⁾	MODE
An	Х	An	\uparrow	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
Х	An	An + 1	\uparrow	Н	L ⁽⁵⁾	Н	Dvo(n+1)	Counter Enabled—Internal Address generation
Х	An + 1	An + 1	\uparrow	Н	Н	Н	Dvo(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
Х	Х	An	\uparrow	Х	Х	L ⁽⁴⁾	Dvo(0)	Counter Set to last valid ADS load

Truth Table II—Address and Address Counter Control^(1,2,7)

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. Read and write operations are controlled by the appropriate setting of R/W, CEo, CE1, UB/LB and OE.

3. Outputs configured in flow-through output mode: if outputs are in pipelined mode the data out will be delayed by one cycle.

4. ADS and REPEAT are independent of all other memory control signals including CEo, CE1 and UB/LB

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other memory control signals including CE0, CE1, UB/LB.

6. When REPEAT is asserted, the counter will reset to the last valid address loaded via ADS. This value is not set at power-up: a known location should be loaded via ADS during initialization if desired. Any subsequent ADS access during operations will update the REPEAT address location.

7. The counter includes bank address and internal address. The counter will advance across bank boundaries. For example, if the counter is in Bank 0, at address FFFh, and is advanced one location, it will move to address 0h in Bank 1. By the same token, the counter at FFFh in Bank 63 will advance to 0h in Bank 0. Refer to Timing Waveform of Counter Repeat, page 17. Care should be taken during operation to avoid having both counters point to the same bank (i.e., ensure BAoL - BA5L ≠ BAOR - BA5R), as this condition will invalidate the access for both ports. Please refer to the functional description on page 18 for details.

5628 tbl 02

5628 tbl 03

IDT70V7339S

High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 150mV
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 150mV

NOTE:

1. This is the parameter TA. This is the "instant on" case temperature.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
Ιουτ	DC Output Current	50	mA
NOTEO			5628 tbl 06

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

 VTERM must not exceed VDD + 150mV for more than 25% of the cycle time or 4ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ VDD + 150mV.

Recommended DC Operating Conditions with VDDQ at 2.5V

Symbol	Parameter	Min.	Тур.	Мах.	Unit		
Vdd	Core Supply Voltage	3.15	3.3	3.45	۷		
VDDQ	I/O Supply Voltage ⁽³⁾	2.4	2.5	2.6	V		
Vss	Ground	0	0	0	V		
Vih	Input High Voltage (Address & Control Inputs)	1.7	-	Vddq + 100mV ⁽²⁾	V		
Vih	Input High Voltage - I/O ⁽³⁾	1.7	-	$V_{DDQ} + 100 mV^{(2)}$	V		
Vil	Input Low Voltage	-0.3(1)	-	0.7	V		
5628 tbl							

NOTES:

5628 tbl 04

1. Undershoot of VIL $_{\geq}$ -1.5V for pulse width less than 10ns is allowed.

2. VTERM must not exceed VDDQ + 100mV.

 To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIL (0V), and VDDOX for that port must be supplied as indicated above.

Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vdd	Core Supply Voltage	3.15	3.3	3.45	V
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	V
Vss	Ground	0	0	0	V
Vih	Input High Voltage (Address & Control Inputs) ⁽³⁾	2.0	_	Vddq + 150mV ⁽²⁾	V
Vih	Input High Voltage - I/O ⁽³⁾	2.0	_	$V_{DDQ} + 150 mV^{(2)}$	V
VIL	Input Low Voltage	-0.3(1)	_	0.8	V

Recommended DC Operating Conditions with VDDQ at 3.3V

NOTES:

- 1. Undershoot of VIL $_{\geq}$ -1.5V for pulse width less than 10ns is allowed.
- 2. VTERM must not exceed VDDQ + 150mV.
- 3. To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIH (3.3V), and VDDox for that port must be supplied as indicated above.

5628 tbl 05b

IDT70V7339S High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

5628 tbl 08

Capacitance⁽¹⁾

Symbol	Parameter	Conditions ⁽²⁾	Мах.	Unit						
Cin	Input Capacitance	ViN = 3dV	8	pF						
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10.5	pF						
5628 tbl 07										

 $(TA = +25^{\circ}C, F = 1.0MHz) PQFP ONLY$

NOTES:

1. These parameters are determined by device characterization, but are not production tested.

2. 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

3. COUT also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = $3.3V \pm 150$ mV)

			70V7	3395	
Symbol	Parameter Test Conditions		Min.	Мах.	Unit
ILI	Input Leakage Current ⁽¹⁾	$V_{DDQ} = Max., V_{IN} = 0V$ to V_{DDQ}		10	μA
Ilo	Output Leakage Current ⁽¹⁾	\overline{CE}_0 = Vih or CE1 = Vil, Vout = 0V to VDDQ		10	μA
Vol (3.3V)	Output Low Voltage ⁽²⁾	IOL = +4mA, $VDDQ = Min$.		0.4	V
Vон (3.3V)	Output High Voltage ⁽²⁾	Ioh = -4mA, VDDQ = Min.	2.4		V
Vol (2.5V)	Output Low Voltage ⁽²⁾	IOL = +2mA, $VDDQ = Min$.		0.4	V
Vон (2.5V)	Output High Voltage ⁽²⁾	Ioh = -2mA, VDDQ = Min.	2.0		V

NOTES:

1. At VDD \leq 2.0V leakages are undefined.

2. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to page 4 for details.

High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁵⁾ ($V_{DD} = 3.3V \pm 150 \text{mV}$)

						9S200 ⁽⁷⁾ I Only	Co	9S166 ⁽⁶⁾ m'I Ind	70V7339S133 Com'l & Ind		
Symbol	Parameter	Test Condition	Versio	on	Тур. ⁽⁴⁾	Мах	Typ. ⁽⁴⁾	Мах.	Тур. ⁽⁴⁾	Мах.	Unit
IDD	Dynamic Operating	CEL and CER= VIL,	COM'L	S	815	950	675	790	550	645	mA
	Current (Both Ports Active)	Outputs Disabled, f = fMAX ⁽¹⁾	IND	S			675	830	550	675	1
ISB1	Standby Current	$\overline{CEL} = \overline{CER} = VH$	COM'L	S	340	410	275	340	250	295	mA
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	S	_		275	355	250	310]
ISB2	Standby Current	$\overline{CE}^*A^* = VIL \text{ and } \overline{CE}^*B^* = VIH^{(3)}$	COM'L	S	690	770	515	640	460	520	mA
	(One Port - TTL Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S	_	_	515	660	460	545]
ISB3	Full Standby Current	Both Ports \overline{CEL} and $\overline{CER} \ge VDDQ - 0.2V$,	COM'L	S	10	30	10	30	10	30	mA
	(Both Ports - CMOS Level Inputs)	$\label{eq:VIN_solution} \begin{array}{l} \text{VIN} \geq \text{VDDQ} - 0.2 \text{V} \text{ or } \text{VIN} \leq 0.2 \text{V}, \\ f = 0^{(2)} \end{array}$	IND	S	_		10	40	10	40	
ISB4	Full Standby Current (One Port - CMOS	$\overline{CE}^*A^* \le 0.2V$ and $\overline{CE}^*B^* \ge VDDQ - 0.2V^{(5)}$ VIN $\ge VDDQ - 0.2V$ or VIN $\le 0.2V$,	COM'L	S	690	770	515	640	460	520	mA
	Level Inputs)	Active Port, Outputs Disabled, f = fMAX ⁽¹⁾	IND	S			515	660	460	545	
										56	528 tbl 09

NOTES:

1. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. <u>VDD</u> = 3.3V, TA = $25^{\circ}C$ for Typ, and are not production tested. IDD DC(f=0) = 120mA (Typ).
- 5. $\overline{CEx} = VIL$ means $\overline{CEox} = VIL$ and CE1x = VIH
 - $\begin{array}{|c|c|c|c|c|} \hline CEx = V\text{IH} \mbox{ means } \hline CEx = V\text{IH} \mbox{ or } CE1x = V\text{IL} \\ \hline CEx \leq 0.2V \mbox{ means } \hline CEx \leq 0.2V \mbox{ and } CE1x \geq V\text{DDQ} \mbox{ } 0.2V \\ \hline CEx \geq V\text{DDQ} \mbox{ } 0.2V \mbox{ means } \hline CEx \geq V\text{DDQ} \mbox{ } 0.2V \mbox{ or } CE1x \leq 0.2V \\ \hline \end{array}$
- "X" represents "L" for left port or "R" for right port.
- 6. 166MHz Industrial Temperature not available in BF-208 package.
- 7. This speed grade available when VDD0 = 3.3.V for a specific port (i.e., OPTx = VIH). This speed grade is available in BC-256 only.

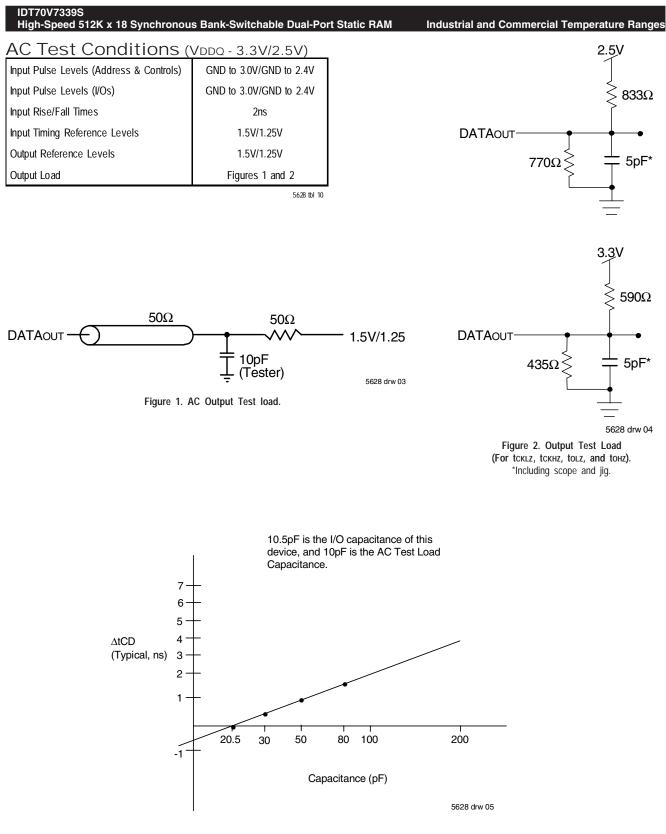


Figure 3. Typical Output Derating (Lumped Capacitive Load).

High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)^(2,3) (V_{DD} = $3.3V \pm 150$ mV, TA = 0°C to +70°C)

	and write Cycle Timing) $(2,3)$ (VDD = 3.3V ±		70V7339S200 ⁽⁵⁾ Com'l Only		70V7339S166 ^(3,4) Com'l & Ind		70V7339S133 ⁽³⁾ Com'l & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Мах.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽¹⁾	15	_	20		25		ns
tcyc2	Clock Cycle Time (Pipelined) ⁽¹⁾	5	_	6		7.5		ns
tCH1	Clock High Time (Flow-Through) ⁽¹⁾	5	_	6		7		ns
tCL1	Clock Low Time (Flow-Through) ⁽¹⁾	5	_	6		7		ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	2.0	_	2.1		2.6		ns
tCL2	Clock Low Time (Pipelined) ⁽¹⁾	2.0	_	2.1		2.6		ns
tR	Clock Rise Time	_	1.5		1.5		1.5	ns
tr	Clock Fall Time		1.5		1.5		1.5	ns
tsa	Address Setup Time	1.5	_	1.7		1.8		ns
tha	Address Hold Time	0.5	_	0.5		0.5		ns
tsc	Chip Enable Setup Time	1.5	_	1.7		1.8		ns
tнc	Chip Enable Hold Time	0.5	_	0.5		0.5		ns
tsв	Byte Enable Setup Time	1.5	_	1.7		1.8		ns
tнв	Byte Enable Hold Time	0.5	_	0.5		0.5		ns
tsw	R/W Setup Time	1.5	_	1.7		1.8		ns
thw	R/W Hold Time	0.5	_	0.5		0.5		ns
tsp	Input Data Setup Time	1.5	_	1.7		1.8		ns
thd	Input Data Hold Time	0.5	_	0.5		0.5	—	ns
tsad	ADS Setup Time	1.5	_	1.7	—	1.8	—	ns
thad	ADS Hold Time	0.5	_	0.5		0.5		ns
tscn	CNTEN Setup Time	1.5		1.7		1.8		ns
then	CNTEN Hold Time	0.5	_	0.5		0.5		ns
t SRPT	REPEAT Setup Time	1.5	_	1.7		1.8		ns
T HRPT	REPEAT Hold Time	0.5	_	0.5		0.5	—	ns
toe	Output Enable to Data Valid		4.0		4.0		4.2	ns
tolz	Output Enable to Output Low-Z	0.5	_	0.5		0.5		ns
toнz	Output Enable to Output High-Z	1	3.4	1	3.6	1	4.2	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽¹⁾		10		12		15	ns
tCD2	Clock to Data Valid (Pipelined) ⁽¹⁾		3.4		3.6		4.2	ns
tDC	Data Output Hold After Clock High	1	_	1		1		ns
tскнz	Clock High to Output High-Z	1	3.4	1	3.6	1	4.2	ns
tскız	Clock High to Output Low-Z	0.5		0.5		0.5		ns
Port-to-Port D	Jelay	•			-			e
tco	Clock-to-Clock Offset	5.0	_	6.0		7.5		ns

NOTES:

2. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE) and FT/PIPEx. FT/PIPEx should be treated as a DC signal, i.e. steady state during operation.

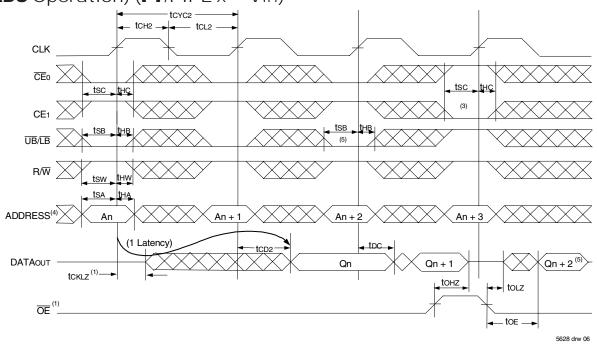
3. These values are valid for either level of VDDQ (3.3V/2.5V). See page 4 for details on selecting the desired operating voltage levels for each port.

4. 166MHz Industrial Temperature not available in BF-208 package.

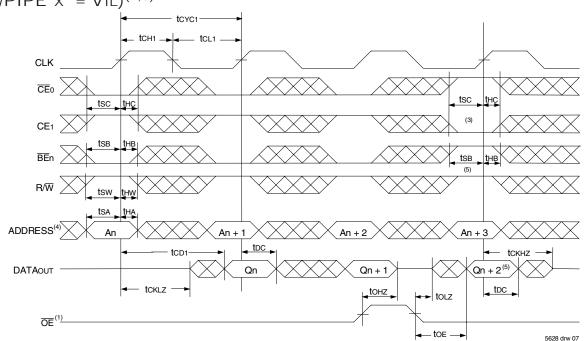
5. This speed grade available when VDD0 = 3.3.V for a specific port (i.e., OPTx = VIH). This speed grade available in BC-256 package only.

^{1.} The Pipelined output parameters (tcvc2, tcb2) apply to either or both left and right ports when \overline{FT} /PIPEx = VIH. Flow-through parameters (tcvc1, tcb1) apply when \overline{FT} /PIPEx = VIH for that port.

Timing Waveform of Read Cycle for Pipelined Operation (ADS Operation) (\overline{FT} /PIPE'x' = VIH)⁽²⁾

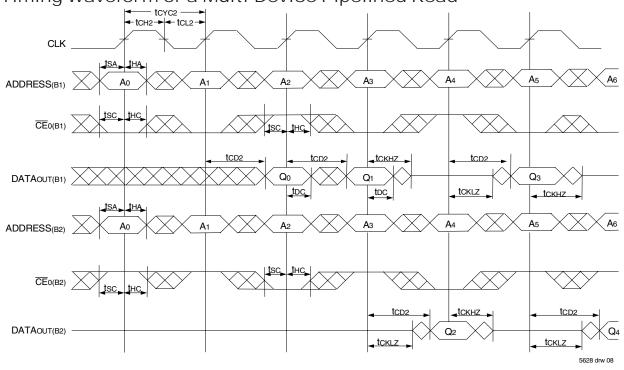




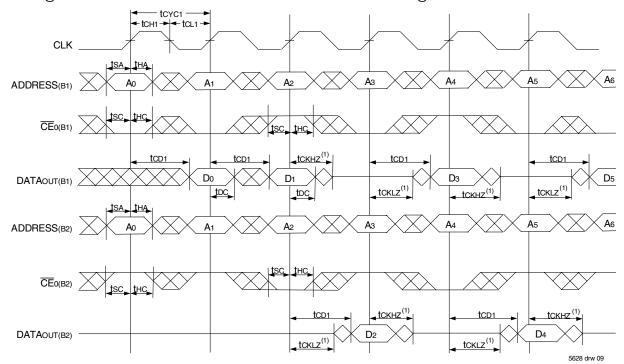


- 1. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 2. ADS = VIL, CNTEN and REPEAT = VIH.
- 3. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{IH}$, $CE_1 = V_{IL}$, $\overline{UB}/\overline{LB} = V_{IH}$ following the next rising edge of the clock. Refer to Truth Table 1.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. If UB/LB was HIGH, then the appropriate Byte of DATAout for Qn + 2 would be disabled (High-Impedance state).
- 6. "x" denotes Left or Right port. The diagram is with respect to that port.





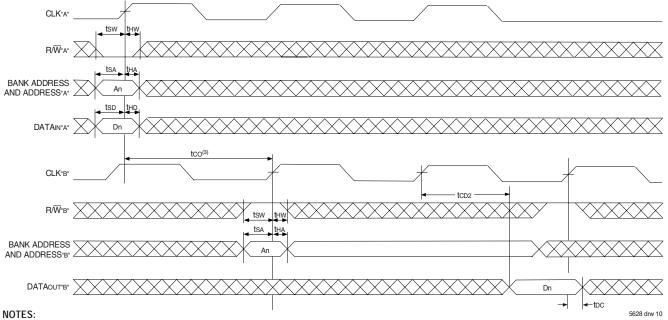
Timing Waveform of a Multi-Device Flow-Through Read^(1,2)



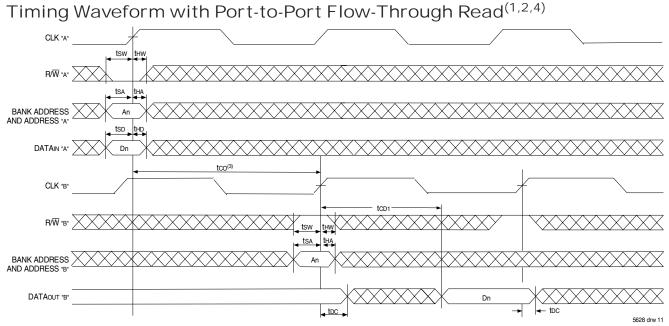
- 1. B1 Represents Device #1; B2 Represents Device #2. Each Device consists of one IDT70V7339 for this waveform,
- and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{UB}/\overline{LB}$, \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W, \overline{CNTEN} , and \overline{REPEAT} = VIH.

Dual-Port Static RAM Industrial and Commercial Temperature Ranges

Timing Waveform of Port A Write to Pipelined Port B Read^(1,2,4)

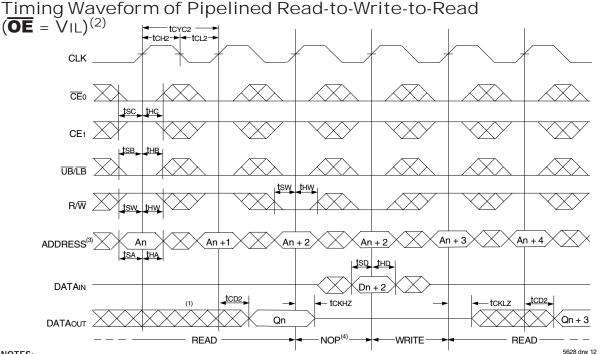


- 1. \overline{CE}_{0} , \overline{BE}_{n} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{REPEAT} = VIH.
- 2. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.
- 3. If tco < minimum specified, then operations from both ports are INVALID. If tco ≥ minimum, then data from Port "B" read is available on first Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + tcyc2 + tcp2).
- 4. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".



- 1. \overline{CE}_{0} , \overline{BE}_{n} , and $\overline{ADS} = VIL$; CE1, \overline{CNTEN} , and $\overline{REPEAT} = VIH$.
- 2. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.
- 3. If tco < minimum specified, then operations from both ports are INVALID. If tco ≥ minimum, then data from Port "B" read is available on first Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcb1).
- 4. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

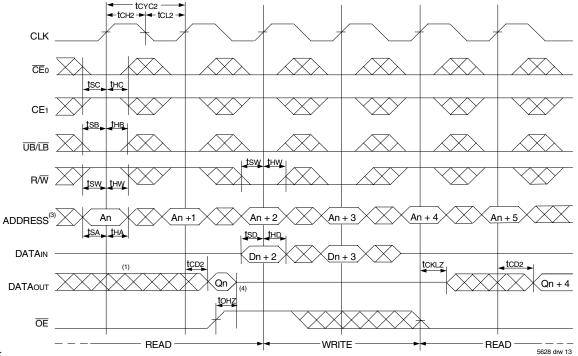
High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM Industrial and Commercial Temperature Ranges



NOTES:

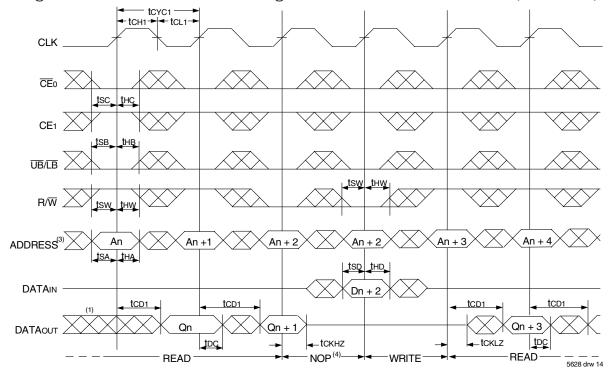
- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals. 2. $\overline{CE_0}$, $\overline{BE_n}$, and $\overline{ADS} = V_{IL}$; CE_1 , \overline{CNTEN} , and $\overline{REPEAT} = V_{IH}$. "NOP" is "No Operation".
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers 3. are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to quarantee data integrity.

Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽²⁾

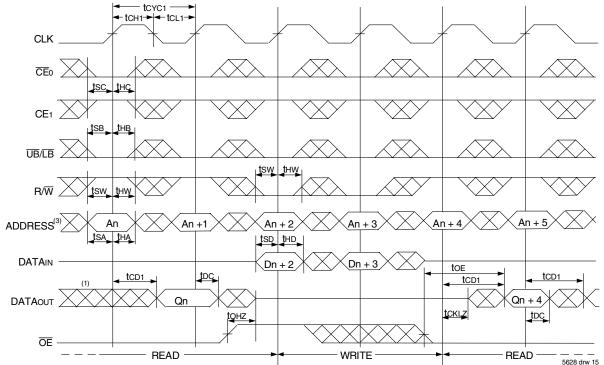


- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- CEO, UB/LB, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH. 2.
- 3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. This timing does not meet requirements for fastest speed grade. This waveform indicates how logically it could be done if timing so allows.

Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽²⁾



Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽²⁾



NOTES:

1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.

2. CEo, UB/LB, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH.

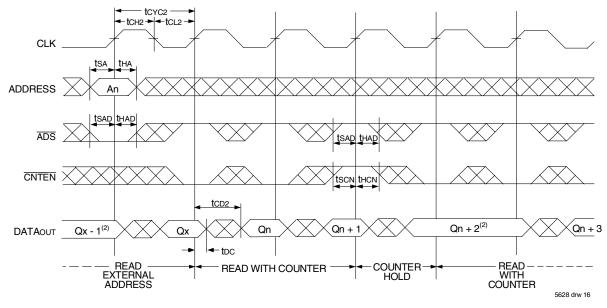
3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.

4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

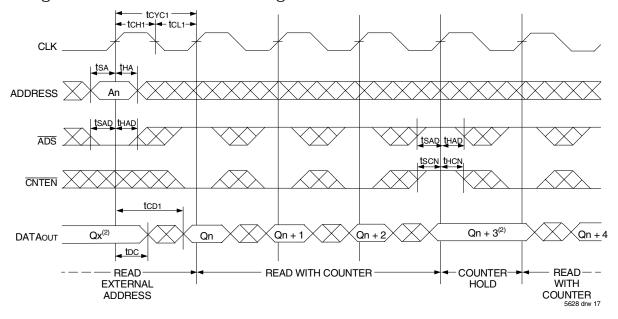
IDT70V7339S High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

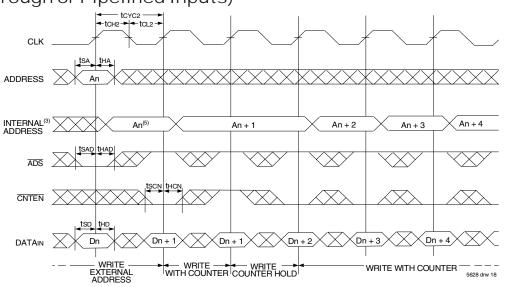


 $Timing \, Waveform \, of \, Flow-Through \, Read \, with \, Address \, Counter \, Advance^{(1)}$

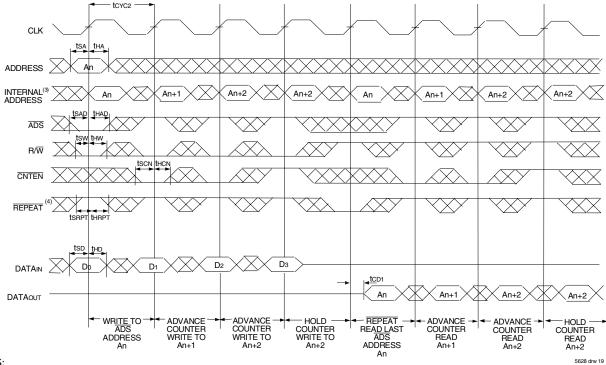


- 1. \overline{CE}_{0} , \overline{OE} , $\overline{UB}/\overline{LB}$ = VIL; CE1, R/W, and \overline{REPEAT} = VIH.
- 2. If there is no address change via $\overline{\text{ADS}}$ = VIL (loading a new address) or $\overline{\text{CNTEN}}$ = VIL (advancing the address), i.e. $\overline{\text{ADS}}$ = VIH and $\overline{\text{CNTEN}}$ = VIH, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-through or Pipelined Inputs)^(1,6)



Timing Waveform of Counter Repeat for Flow Through Mode^(2,6,7)



- 1. \overline{CE}_{0} , $\overline{UB}/\overline{LB}$, and $R/\overline{W} = V_{IL}$; CE1 and $\overline{REPEAT} = V_{IH}$.
- 2. \overline{CE}_{0} , $\overline{UB}/\overline{LB}$ = VIL; CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when $\overline{ADS} = V_{IL}$ and equals the counter output when $\overline{ADS} = V_{IH}$.
- 4. No dead cycle exists during REPEAT operation. A READ or WRITE cycle may be coincidental with the counter REPEAT cycle: Address loaded by last valid ADS load will be accessed. For more information on REPEAT function refer to Truth Table II.
- CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.
- 6. The counter includes bank address and internal address. The counter will advance across bank boundaries. For example, if the counter is in Bank 0, at address FFFh, and is advanced one location, it will move to address 0h in Bank 1. By the same token, the counter at FFFh in Bank 63 will advance to 0h in Bank 0.
- 7. For Pipelined Mode user should add 1 cycle latency for outputs as per timing waveform of read cycle for pipelined operations.

IDT70V7339S

High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Functional Description

The IDT70V7339 is a high-speed 512Kx18 (9 Mbit) synchronous Bank-Switchable Dual-Ported SRAM organized into 64 independent 8Kx18 banks. Based on a standard SRAM core instead of a traditional true dual-port memory core, this bank-switchable device offers the benefits of increased density and lower cost-per-bit while retaining many of the features of true dual-ports. These features include simultaneous, random access to the shared array, separate clocks per port, 166 MHz operating speed, full-boundary counters, and pinouts compatible with the IDT70V3319 (256Kx18) dual-port family.

The two ports are permitted independent, simultaneous access into separate banks within the shared array. Access by the ports into specific banks are controlled by the bank address pins under the user's direct control: each port can access any bank of memory with the shared array that is not currently being accessed by the opposite port (i.e., BAOL - BA5L \neq BAOR - BA5R). In the event that both ports try to access the same bank at the same time, neither access will be valid, and data at the two specific addresses targeted by the ports within that bank may be corrupted (in the case that either or both ports are writing) or may result in invalid output (in the case that both ports are trying to read).

The IDT70V7339 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal setup and hold times on address, data and all critical control inputs.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

A HIGH on \overline{CE}_0 or a LOW on CE1 for one clock cycle will power down the internal circuitry on each port (individually controlled) to reduce static power consumption. Dual chip enables allow easier banking of multiple IDT70V7339s for depth expansion configurations. Two cycles are required with CE0 LOW and CE1 HIGH to read valid data on the outputs.

Depth and Width Expansion

The IDT70V7339 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT70V7339 can also be used in applications requiring expanded width, as indicated in Figure 4. Through combining the control signals, the devices can be grouped as necessary to accommodate applications needing 36-bits or wider.

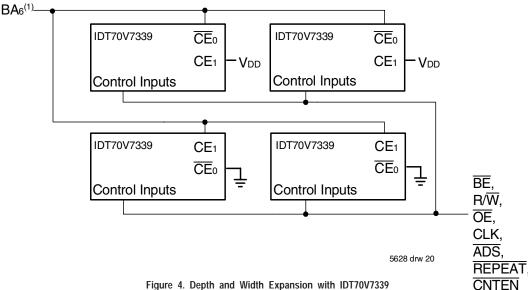


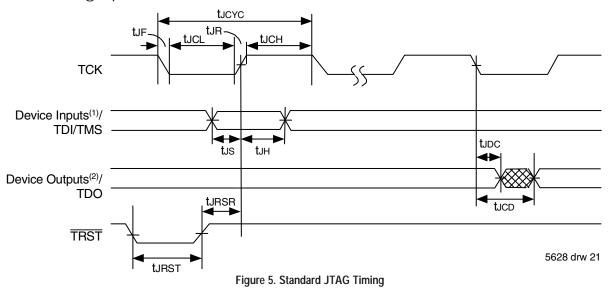
Figure 4. Depth and Width Expansion with IDT70V7339

NOTE:

1. In the case of depth expansion, the additional address pin logically serves as an extension of the bank address. Accesses by the ports into specific banks are controlled by the bank address pins under the user's direct control: each port can access any bank of memory within the shared array that is not currently being accessed by the opposite port (i.e., BAoL - BAoL ≠ BAoR - BAoR). In the event that both ports try to access the same bank at the same time, neither access will be valid, and data at the two specific addresses targeted by the parts within that bank may be corrupted (in the case that either or both parts are writing) or may result in invalid output (in the case that both ports are trying to read).

High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM

JTAG Timing Specifications



NOTES:

1. Device inputs = All device inputs except TDI, TMS, TRST, and TCK.

2. Device outputs = All device outputs except TDO.

Cł	Characteristics ^(1,2,3,4)					
			70V7339			
	Symbol	Parameter	Min.	Мах.		
	tucyc	JTAG Clock Input Period	100			
	рсн	JTAG Clock HIGH	40			
	ticl	JTAG Clock Low	40			
	tjr	JTAG Clock Rise Time		3(1)		
	IJF	JTAG Clock Fall Time		3(1)		
	U RST	JTAG Reset	50			

JTAG Reset Recovery

JTAG Data Output

JTAG Data Output Hold

JTAG Setup

JTAG Hold

JTAG AC Electrical Characteristics^(1,2,3,4)

ns			
5628 tbl	12		

Units

ns ns ns

ns

ns

ns

ns

ns

ns

ns

25

50

_

0

15

15

NOTES: 1. Guaranteed by design.

tursr

ticd

tudc

tıs

tлн

2. 30pF loading on external output signals.

3. Refer to AC Electrical Test Conditions stated earlier in this document.

4. JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.

IDT70V7339S High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Identification Register Definitions

Instruction Field	Value	Description
Revision Number (31:28)	0x0	Reserved for version number
IDT Device ID (27:12)	0x301	Defines IDT part number
IDT JEDEC ID (11:1)	0x33	Allows unique identification of device vendor as IDT
ID Register Indicator Bit (Bit 0)	1	Indicates the presence of an ID register

5628 tbl 13

5628 tbl 15

Scan Register Sizes

Register Name	Bit Size
Instruction (IR)	4
Bypass (BYR)	1
Identification (IDR)	32
Boundary Scan (BSR)	Note (3)

5628 tbl 14

System Interface Parameters

Instruction	Code	Description
EXTEST	0000	Forces contents of the boundary scan cells onto the device outputs ⁽¹⁾ . Places the boundary scan register (BSR) between TDI and TDO.
BYPASS	1111	Places the bypass register (BYR) between TDI and TDO.
IDCODE	0010	Loads the ID register (IDR) with the vendor ID code and places the register between TDI and TDO.
HIGHZ	0100	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers to a High-Z state.
CLAMP	0011	Uses BYR. Forces contents of the boundary scan cells onto the device outputs. Places the bypass register (BYR) between TDI and TDO.
SAMPLE/PRELOAD	0001	Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ⁽²⁾ and outputs ⁽¹⁾ to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.
RESERVED	All other codes	Several combinations are reserved. Do not use codes other than those identified above.

NOTES:

1. Device outputs = All device outputs except TDO.

2. Device inputs = All device inputs except TDI, TMS, TRST, and TCK.

3. The Boundary Scan Descriptive Language (BSDL) file for this device is available on the IDT website (www.idt.com), or by contacting your local IDT sales representative.

IDT70V7339S High-Speed 512K x 18 Synchronous Bank-Switchable Dual-Port Static RAM Industrial and Commercial Temperature Ranges Ordering Information XXXXX А 999 А А А Process/ Temperature Range Device Power Speed Package Type Commercial (0°C to +70°C) Industrial (-40°C to +85°C) Blank G⁽³⁾ Green BF BC 208-pin fpBGA (BF-208) 256-pin BGA (BC-256) Commercial Only⁽¹⁾ 200 166 133 Commercial & Industrial⁽²⁾ Speed in Megahertz Commercial & Industrial S Standard Power 70V7339 9Mbit (512K x 18-Bit) Synchronous Bank-Switchable Dual-Port RAM

NOTES:

1. Available in BC-256 package only.

2. Industrial Temperature at 166MHz not available in the BF-208 package.

3. Green parts available. For specific speeds, packages and powers contact your local sales office.

Datasheet Document History:

1/5/00:	Initial Public Offering				
6/20/01:	Page 1 Added JTAG information for TQFP package				
	Page 4 & 22 Changed TQFP package from DA to DD				
	Corrected Pin number on TQFP package from 100 to 110				
	Page 20 Increased tuch from 20ns to 25ns				
8/6/01:	Page 4 Changed body size for DD package from 22mm x 22mm x1.6mm to 20mm x 20mm x 1.4mm				
	Page 9 Changed IsB3 values for commercial and industrial DC Electrical Characteristics				
11/20/01:	Page 2, 3 & 4 Added date revision for pin configurations				
	Page 11 Changed toE value in AC Electrical Characteristics, please refer to Errata #SMEN-01-05				
	Page 1 & 22 Replaced ™ logo with ® logo				
03/18/02:	Page 1, 9, 11 & 22 Added 200MHZ specification				
	Page 9 Tightened power numbers in DC Electrical Characteristics				
	Page 14 Changed waveforms to show INVALID operation if $tco < minimum$ specified				
	Page 1 - 22 Removed "Preliminary" status				
12/4/02:	Page 9, 11 & 22 Designated 200Mhz speed grade in BC-256 package only				
01/16/04:	Page 11 Added byte enable setup time and byte enable hold time parameters and values to all speed grades in the AC Electrical				
	Characteristics Table				
07/25/08:	Page 9 Corrected a typo in the DC Chars table				
01/29/09:	Page 22 Removed "IDT" from orderable part number				
04/20/10:	Page 1 Added green availability to features				
	Page 21 Added green indicator to ordering information				
	Removed the DD 144-pin TQFP (DD-144) Thin Quad Flatpack per PDN: F-08-01				



CORPORATE HEADQUARTERS 6024 Silver Creek Valley Road San Jose, CA 95138 *for SALES:* 800-345-7015 or 408-284-8200 fax: 408-284-2775 www.idt.com *for Tech Support:* 408-284-2794 DualPortHelp@idt.com

5628 drw 22

The IDT logo is a registered trademark of Integrated Device Technology, Inc.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for SRAM category:

Click to view products by IDT manufacturer:

Other Similar products are found below :

5962-8855206XA CY6116A-35DMB CY7C128A-45DMB CY7C1461KV33-133AXI CY7C199-45LMB CYDM128B16-55BVXIT GS8161Z36DD-200I GS88237CB-200I R1QDA7236ABB-20IB0 RMLV0408EGSB-4S2#AA0 IS64WV3216BLL-15CTLA3 IS66WVE4M16ECLL-70BLI PCF8570P K6T4008C1B-GB70 CY7C1353S-100AXC AS6C8016-55BIN 515712X IS62WV51216EBLL-45BLI IS63WV1288DBLL-10HLI IS66WVE2M16ECLL-70BLI 47L16-E/SN IS66WVE4M16EALL-70BLI IS62WV6416DBLL-45BLI IS61WV102416DBLL-10TLI CY7C1381KV33-100AXC CY7C1381KV33-100BZXI CY7C1373KV33-100AXC CY7C1381KVE33-133AXI CY7C1382KV33-167AXC CY7C4042KV13-933FCXC 8602501XA 5962-3829425MUA 5962-8855206YA 5962-8866201XA 5962-8866201YA 5962-8866204TA 5962-8866206MA 5962-8866207NA 5962-8866208UA 5962-8872502XA 5962-8959836MZA 5962-8959841MZA 5962-9062007MXA 5962-9161705MXA N08L63W2AB7I 7130LA100PDG GS882Z18CD-150I GS81284Z36B-250I M38510/28902BVA IS62WV12816ALL-70BLI